上海贝岭
SHANGHAI BELLING

BLP04N08

MOSFET

1. Description

BLP04N08, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for BMS and high current switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V_{DSS}	85	V
I_D	120	A
$R_{DS(on).typ}$	3	mΩ

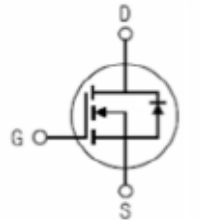
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leqslant 3.6m\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS

- BMS
- Motor drivers

Inner Equivalent Principium Chart



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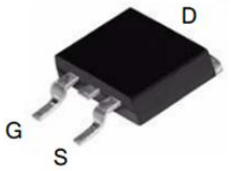


TO-220

1.Gate 2. Drain 3. Source

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
BLP04N08-B	TO-263	P04N08	Reel
BLP04N08-P	TO-220	P04N08	Tube

BLP04N08-B

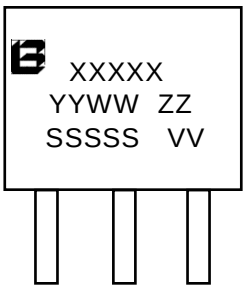
(2) Package type

(1) Chip name

(1) BLP04N08：4mΩ/85V

(2) B：TO-263

P：TO-220



XXXXX：Product Code

YYWW：Year&Week

ZZ：Assembly Code

SSSSS：Lot Code

VV：Classification

2. ABSOLUTE RATINGS

at T_C=25°C，unless otherwise specified

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-Source Voltage	85	V
I_D	Continuous Drain Current, Silicon Limited	185	A
	Continuous Drain Current, Package Limited	120	A
	Continuous Drain Current @T_C=100°C, Silicon Limited	117.2	A
I_{DM} Note1	Pulsed Drain Current	480	A
V_{GS}	Gate-Source Voltage	±20	V
E_{AS} Note2	Avalanche Energy	289	mJ
P_D	Power Dissipation	208.3	W
	Derating Factor above 25°C	1.67	W/℃
T_J， T_{stg}	Operating Junction and Storage Temperature Range	150，–55 to 150	℃
T_L	Maximum Temperature for Soldering	260	℃

Note1：Repetitive Rating：Pulse width limited by maximum junction temperature

Note2：L=0.5mH, Ias=34A, Start T_J=25℃

3. Thermal characteristics

Symbol	Parameter	Max	Units
$R_{\theta JC}$	thermal resistance, Junction-Case	0.6	℃/W
$R_{\theta JA}$	thermal resistance, Junction-Ambient	62.5	℃/W

4. Electrical Characteristics

at T_C=25°C, unless otherwise specified

OFF Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	85	95	--	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=85V, V_{GS}=0V	--	--	1	μA
		V_{DS}=68V, V_{GS}=0V @T_C=125°C	--	--	100	μA
$I_{GSS(F)}$	Gate-Source Forward Leakage	V_{GS}=+20V	--	--	100	nA
$I_{GSS(R)}$	Gate-Source Reverse Leakage	V_{GS}=-20V	--	--	-100	nA

ON Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V, I_D=50A	--	3	3.6	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	2	3	4	V
Pulse width tp≤300μs, δ≤2%						

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
C_{iss}	Input Capacitance	V_{DS}=42.5V, V_{GS}=0, f=1MHz	--	6234	--	pF
C_{oss}	Output Capacitance		--	1181	--	
C_{rss}	Reverse Transfer Capacitance		--	97	--	
Q_g	Total Gate Charge	V_{DD}=42.5V, I_D=50A, V_{GS}=10V	--	124	--	nC
Q_{gs}	Gate-Source charge		--	31.2	--	
Q_{gd}	Gate-Drain charge		--	39.2	--	
R_G	Gate resistance	V_{GS}=0, V_{DS}=0		1.75		Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=42.5V, I_D=10A, V_{GS}=10V, R_G=3Ω, Resistive Load	--	41	--	ns
t_r	Rise Time		--	68	--	
$t_{d(off)}$	Turn-Off Delay Time		--	76	--	
t_f	Fall Time		--	44	--	

Source-Drain Diode Characteristics

Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
I_S	Continuous Source Current		--	--	120	A
I_{SM}	Maximum Pulsed Current		--	--	480	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V, I_S=50A	--	--	1.2	V
T_{rr}	Reverse Recovery Time	I_s=30A, V_{GS}=0, di/dt=100A/us	--	80	--	ns
Q_{rr}	Reverse Recovery Charge		--	112	--	nC

5. Characteristics Curves

Figure 1. Safe Operating Area

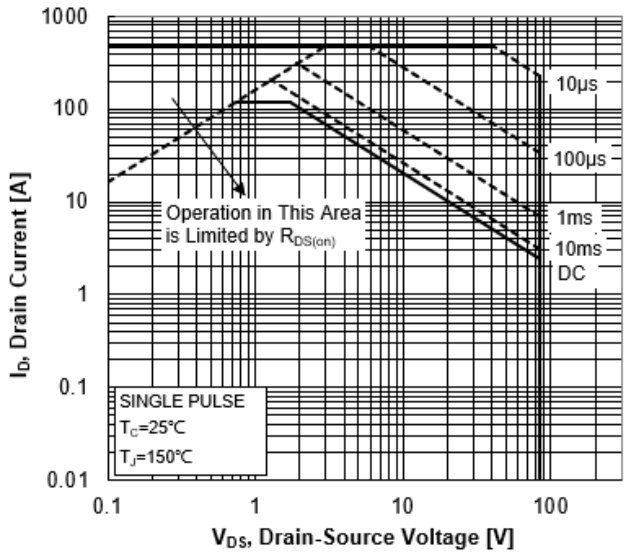


Figure 2. Maximum Power Dissipation vs Case Temperature

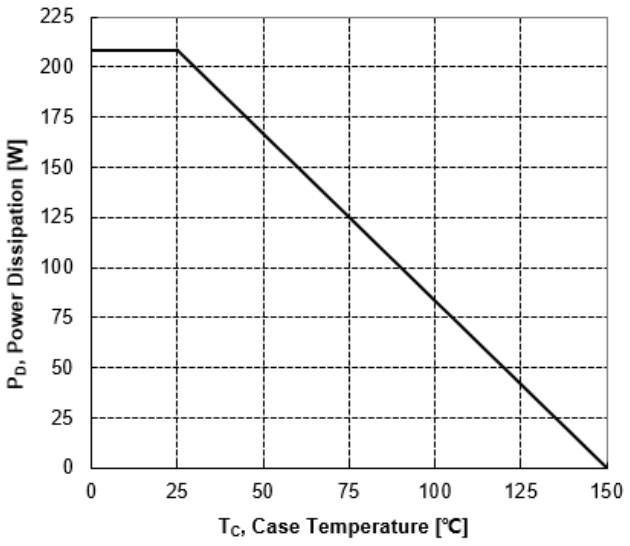


Figure 3. Maximum Continuous Drain Current vs Case Temperature

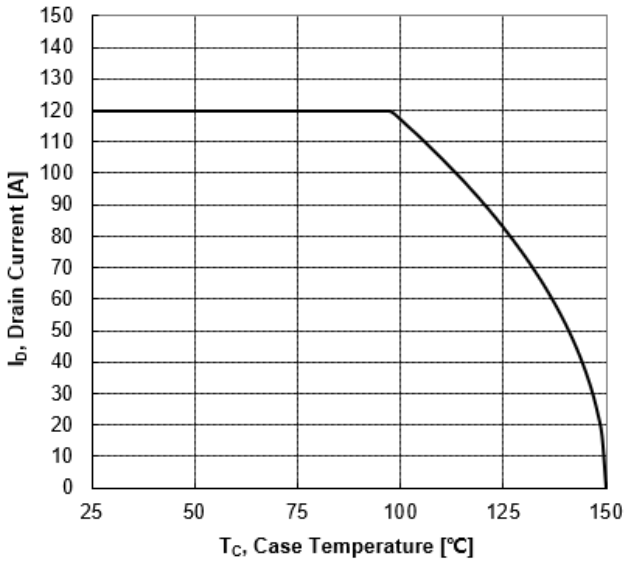


Figure 4. Typical Output Characteristics

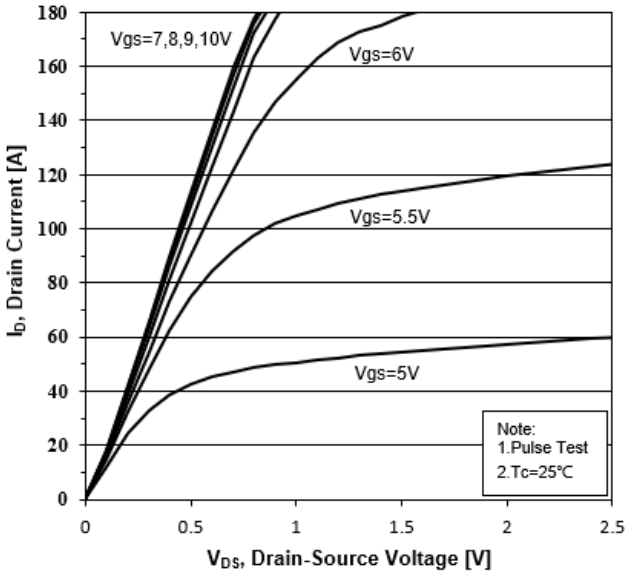


Figure 5. Transient Thermal Impedance

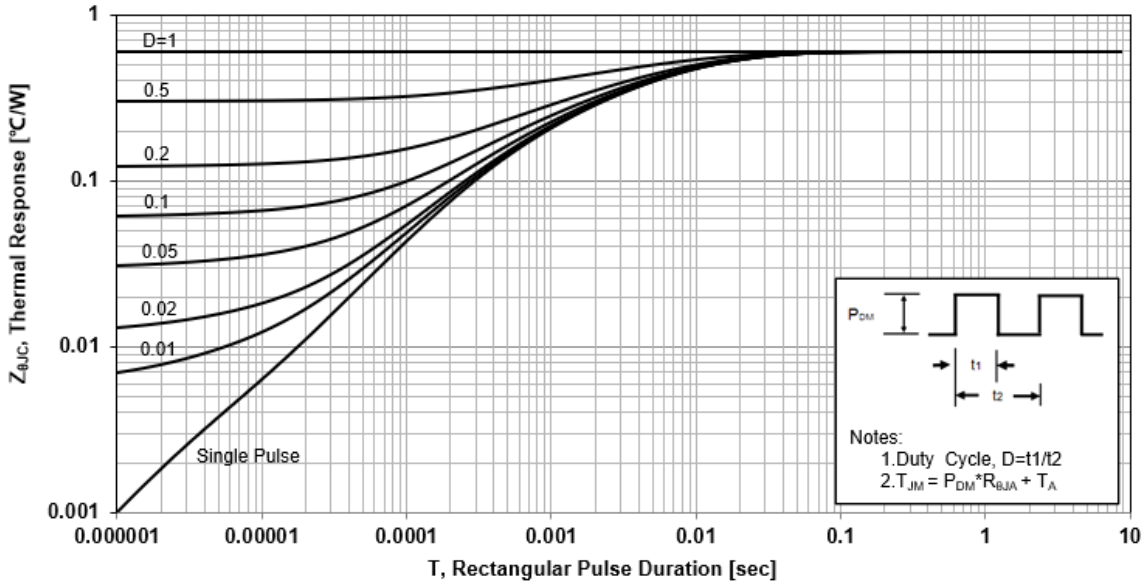


Figure 6. Typical Transfer Characteristics

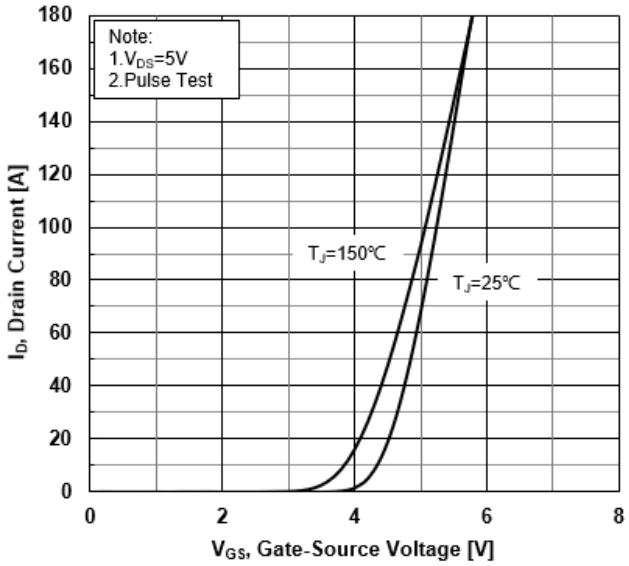


Figure 7. Source-Drain Diode Forward Characteristics

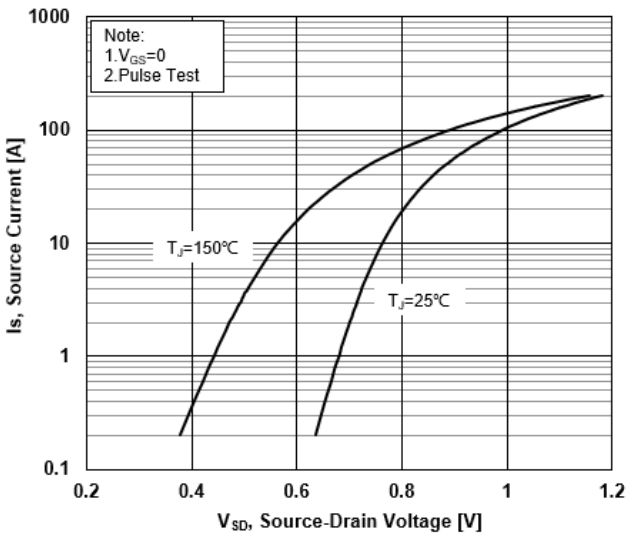


Figure 8. Drain-Source On-Resistance vs Drain Current

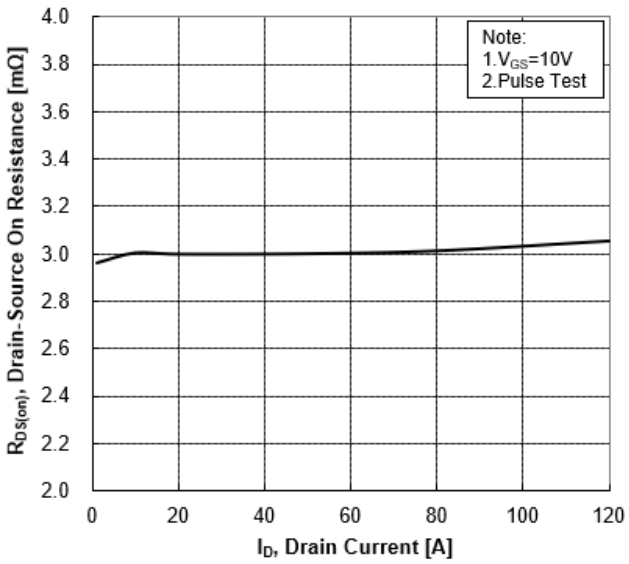


Figure 9. Normalized On-Resistance vs Junction Temperature

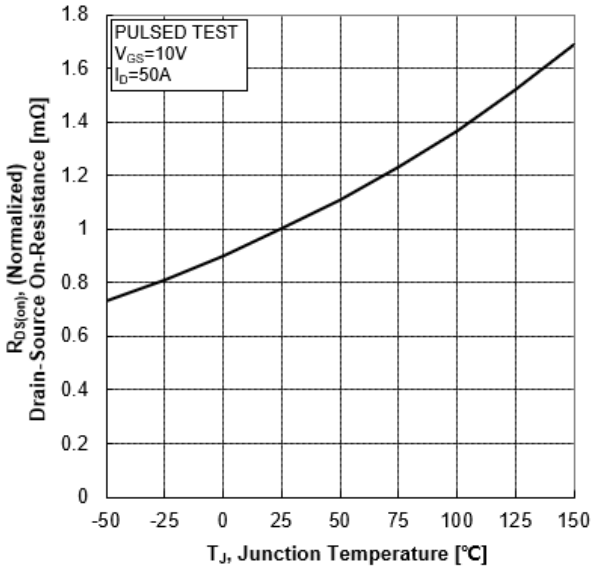


Figure 10. Normalized Threshold Voltage vs Junction Temperature

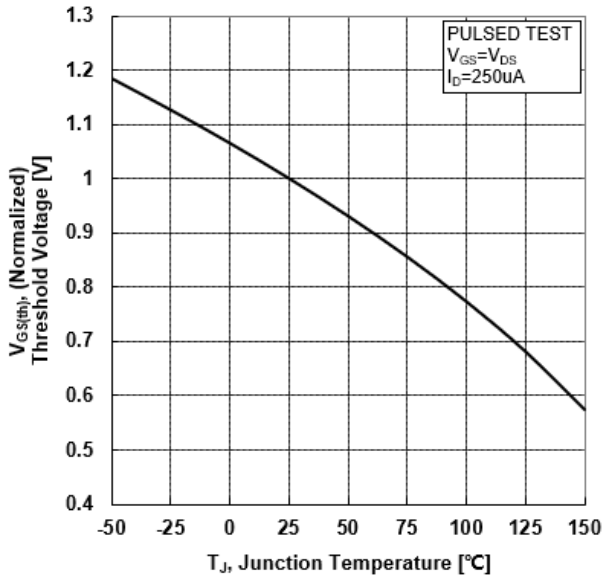


Figure 11. Normalized Breakdown Voltage vs Junction Temperature

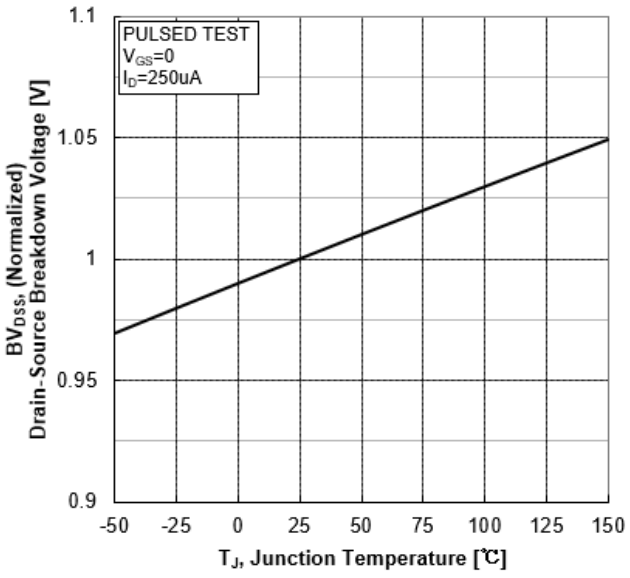


Figure 12. Capacitance Characteristics

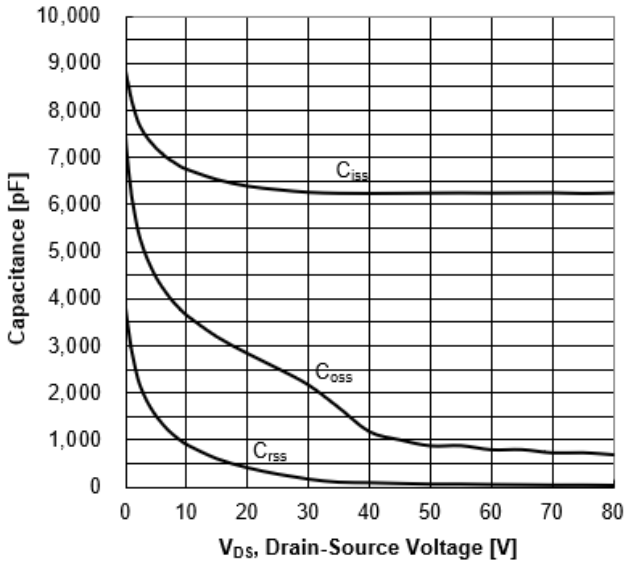
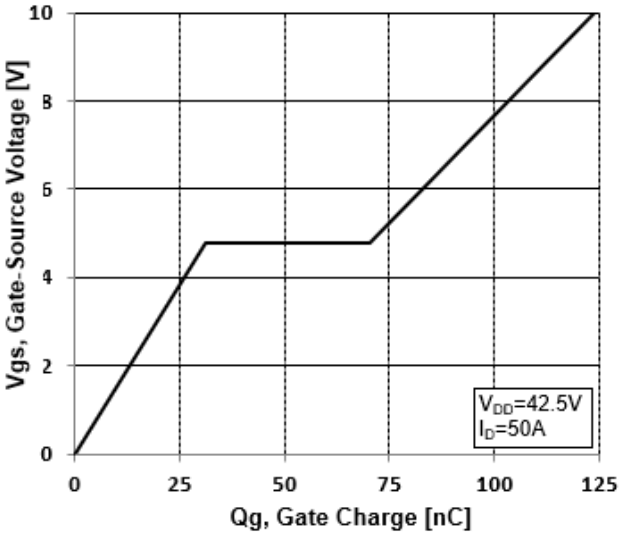


Figure 13. Typical Gate Charge vs Gate-Source Voltage



6. Test Circuit and Waveform

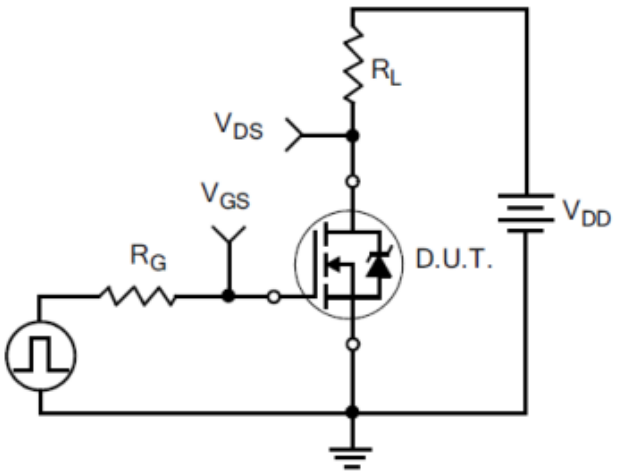
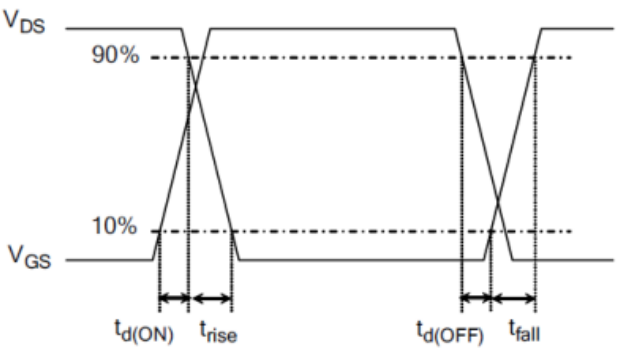
Figure 14. Resistive Switching Test Circuit	Figure 15. Resistive Switching Waveforms
	

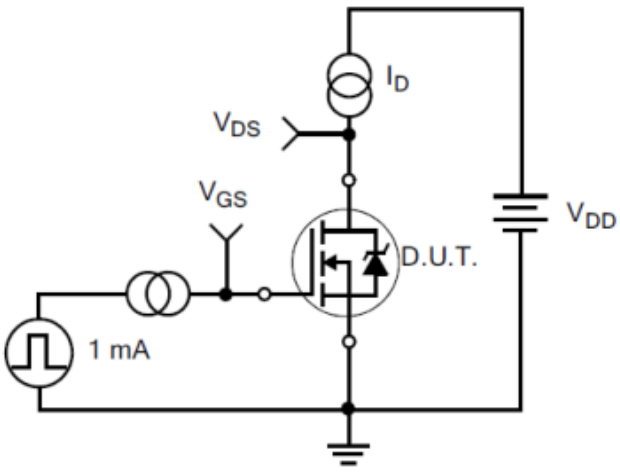
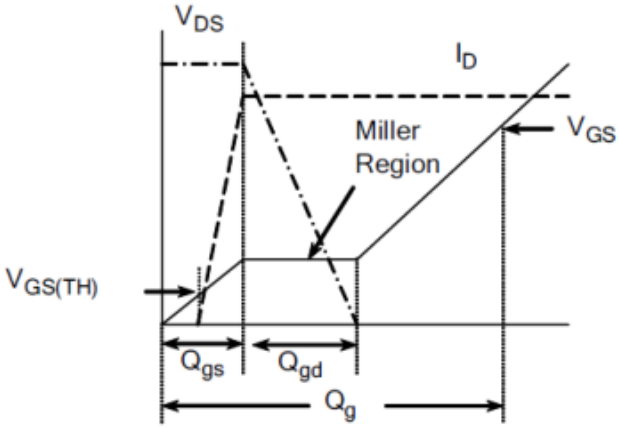
Figure 16. Gate Charge Test Circuit	Figure 17. Gate Charge Waveforms
	

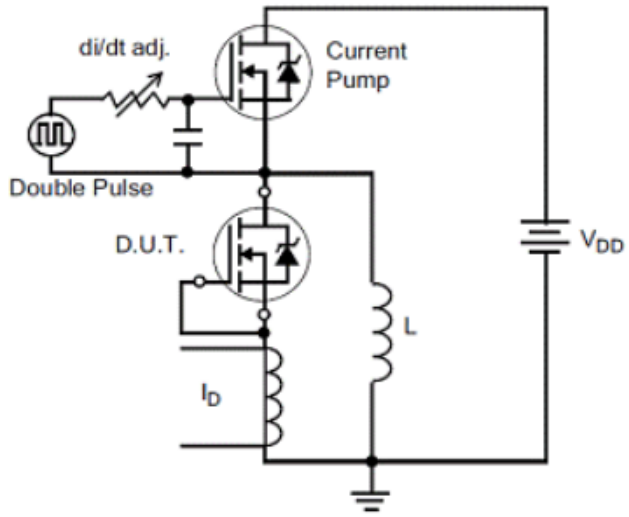
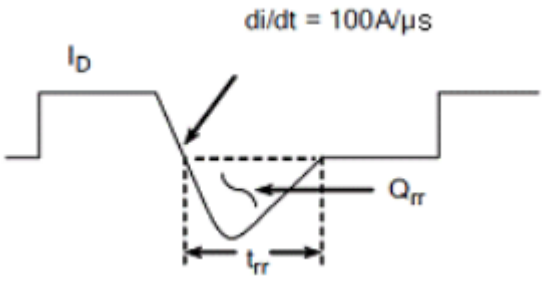
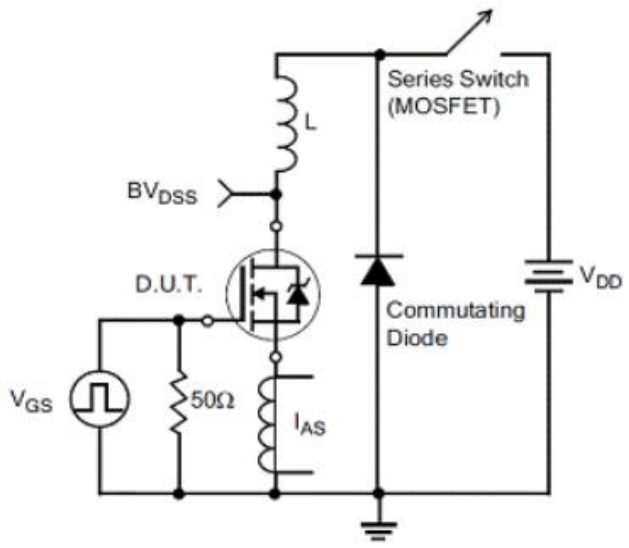
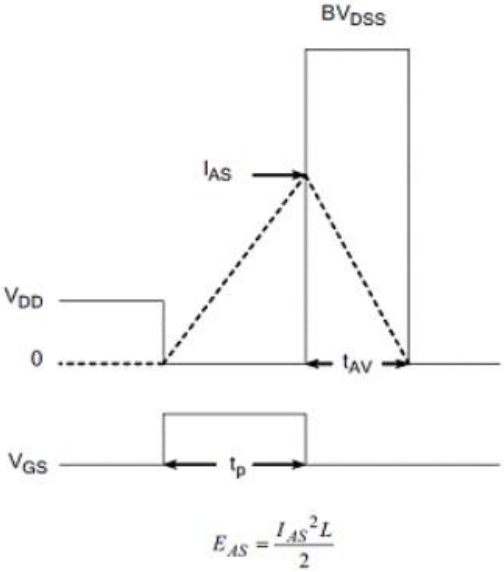
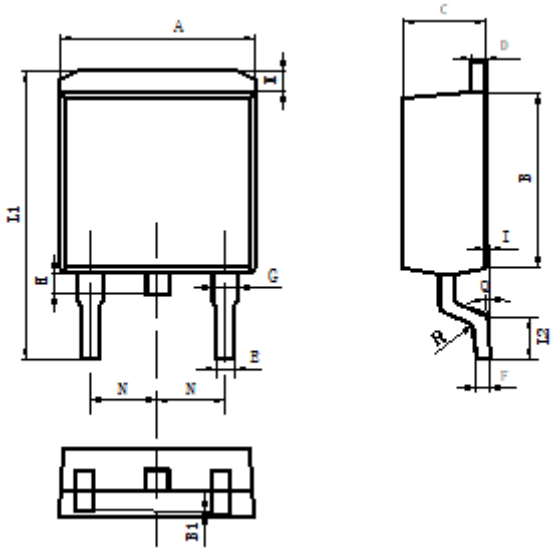
Figure 18. Diode Reverse Recovery Test Circuit	Figure 19. Diode Reverse Recovery Waveform
	

Figure 20. Unclamped Inductive Switching Test Circuit	Figure 21. Unclamped Inductive Switching Waveform
	

$$E_{AS} = \frac{I_{AS}^2 L}{2}$$

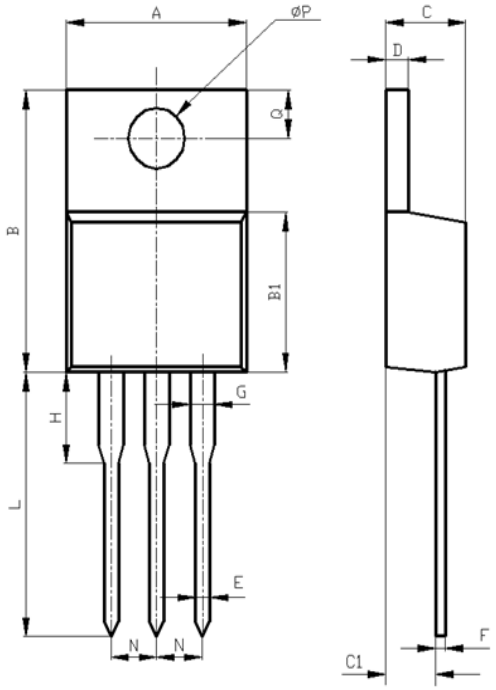
7. Package Description

TO-263



Items	Values(mm)	
	MIN	MAX
A	9.80	10.40
B	8.90	9.50
B1	0	0.10
C	4.40	4.80
D	1.16	1.37
E	0.70	0.95
F	0.30	0.60
G	1.07	1.47
H	1.30	1.80
K	0.95	1.37
L1	14.50	16.50
L2	1.60	2.30
I	0	0.2
Q	0°	8°
R	0.4	0.4
N	2.39	2.69

TO-220



Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
ΦP	3.50	3.90

联系我们

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深圳公司

深圳市泰德兰电子有限公司

地址：深圳市福田区彩田南路 2010 号中深花园 A 座六层

电话：0755-83322522　　传真：0755-83648400

手机：131-89714166　　Q Q：2853781768

香港公司

香港富研科技有限公司

地址：香港葵涌青山公路葵涌段 313 号天际中心 15 楼 1506 室

电话：852-23113966　　邮箱：ll@icbest.com

苏州公司

苏州市泰美兰电子有限公司

地址：苏州姑苏区总官堂路 555 号苏尚新地生活广场 1 幢 802 室

电话：0512-67665578　　邮箱：wg@icbest.com